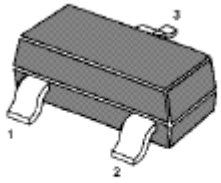
Kingtronics® Kt®

MMBTA92 THRU MMBTA93

PNP Silicon High Voltage Transistors

FEATURES

For high voltage switching and amplifier applications



1. Base 2. Emitter 3. Collector
TO-236 Plastic Package

Absolute Maximum Ratings (T_a = 25℃)

PARAMETER		SYMBOL	VALUE	UNIT
Collector Base Voltage	MMBTA92	$-V_{CBO}$	300	V
	MMBTA93		200	
Collector Emitter Voltage	MMBTA92	$-V_{CEO}$	300	V
	MMBTA93		200	
Emitter Base Voltage		$-V_{EBO}$	5	V
Collector Current		$-I_C$	500	mA
Total Power Dissipation		P_{tot}	350	mW
Junction Temperature		T_j	150	^{0}C
Storage Temperature Range		T_{stg}	- 55 to + 150	^{0}C

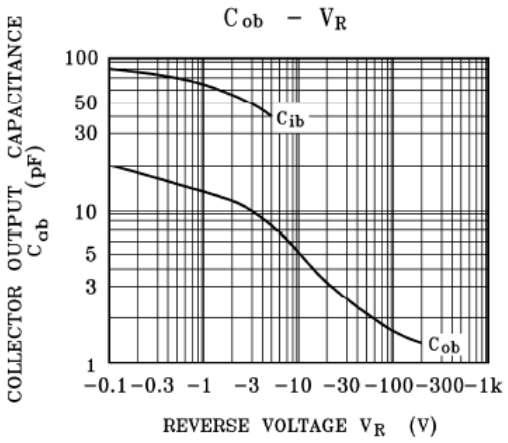
Electrical Characteristics (T_a = 25℃)

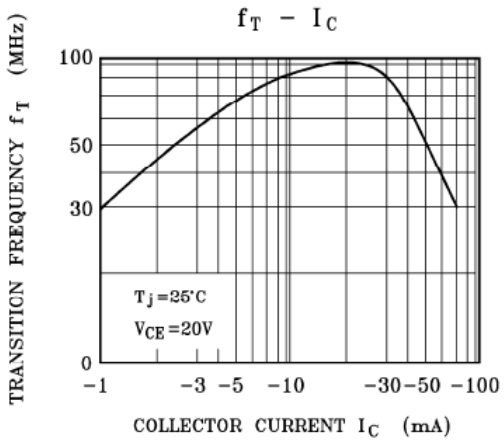
PARAMETER			SYMBOL	Min.	Max.	UNIT
DC Current Gain	at $-V_{CE}$ = 10 V, $-I_C$ = 1 mA		h_{FE}	25	-	-
	at $-V_{CE}$ = 10 V, $-I_C$ = 10 mA		h_{FE}	80	200	-
	at $-V_{CE}$ = 10 V, $-I_C$ = 30 mA		h_{FE}	25	-	-
Collector Base Cutoff Current	at $-V_{CB}$ = 200 V	MMBTA92	$-I_{CBO}$	-	0.25	μA
	at $-V_{CB}$ = 160 V	MMBTA93	$-I_{CBO}$	-	0.25	
Emitter Base Cutoff Current at $-V_{EB}$ = 3 V			$-I_{EBO}$	-	0.1	μA
Collector Base Breakdown Voltage at $-I_C$ = 100 μA	MMBTA92		$-V_{(BR)CBO}$	300	-	V
	MMBTA93		$-V_{(BR)CBO}$	200	-	
Collector Emitter Breakdown Voltage at $-I_C$ = 1 mA	MMBTA92		$-V_{(BR)CEO}$	300	-	V
	MMBTA93		$-V_{(BR)CEO}$	200	-	
Emitter Base Breakdown Voltage at $-I_E$ = 100 μA			$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C$ = 20 mA, $-I_B$ = 2 mA			$-V_{CE(sat)}$	-	0.5	V
Base Emitter Saturation Voltage at $-I_C$ = 20 mA, $-I_B$ = 2 mA			$-V_{BE(sat)}$	-	0.9	V
Current Gain Bandwidth Product at $-V_{CE}$ = 20 V, $-I_C$ = 10 mA, f = 100 MHz			f_T	50	-	MHz
Collector Base Capacitance at -VCB = 20 V, f = 1 MHz	MMBTA92		C_{cb}	-	6	pF
	MMBTA93			-	8	

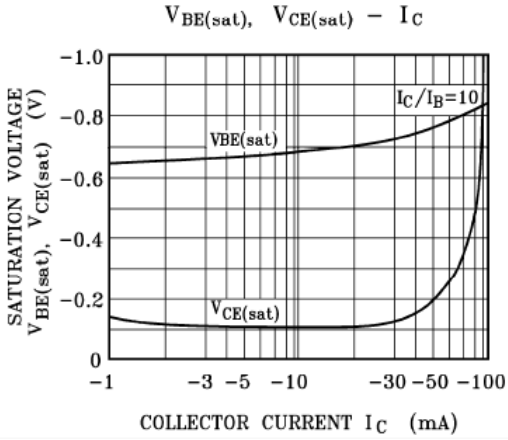
Kingtronics® Kt®

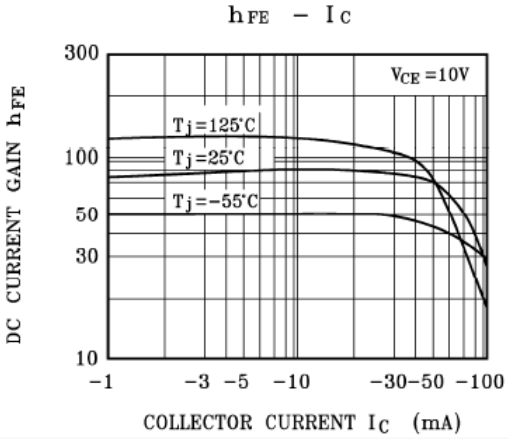
MMBTA92 THRU MMBTA93

PNP Silicon High Voltage Transistors









Note: Specifications are subject to change without notice